

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
20V	28m $\Omega$ @ $V_{GS} = 4.5\text{V}$	7.63A
	41m $\Omega$ @ $V_{GS} = 2.5\text{V}$	4.35A

## Description

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

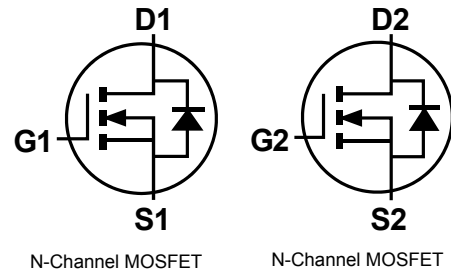
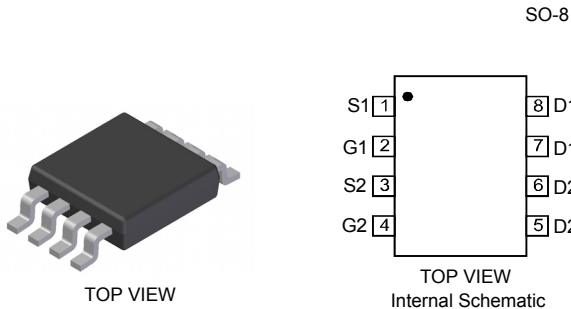
- Power Management Functions
- DC-DC Converters

## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)

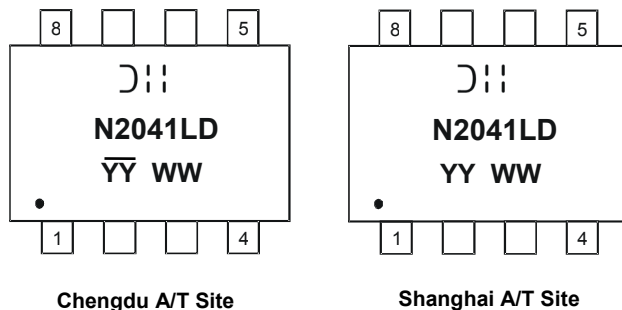


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041LSD-13	SO-8	2,500/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



- ⌋⌋ = Manufacturer's Marking
- N2041LD = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Year (ex: 13 = 2013)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	7.63	A
		T <sub>A</sub> = +85°C		4.92	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	30	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.16	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	R <sub>θJA</sub>	107.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	19	28	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6A
			25	41		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 5.2A
Forward Transfer Admittance	Y <sub>fs</sub>	—	6	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	550	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	88	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	81	—		
Gate Resistance	R <sub>g</sub>	—	1.34	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	15.6	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A
Total Gate Charge	Q <sub>g</sub>	—	7.2	—	nC	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A
Gate-Source Charge	Q <sub>gs</sub>	—	1	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	4.69	—	ns	V <sub>DD</sub> = 10V, V <sub>GEN</sub> = 4.5V, R <sub>g</sub> = 1Ω, I <sub>D</sub> = 6.7A
Turn-On Rise Time	t <sub>r</sub>	—	13.19	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	22.1	—		
Turn-Off Fall Time	t <sub>f</sub>	—	6.43	—		

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by function temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

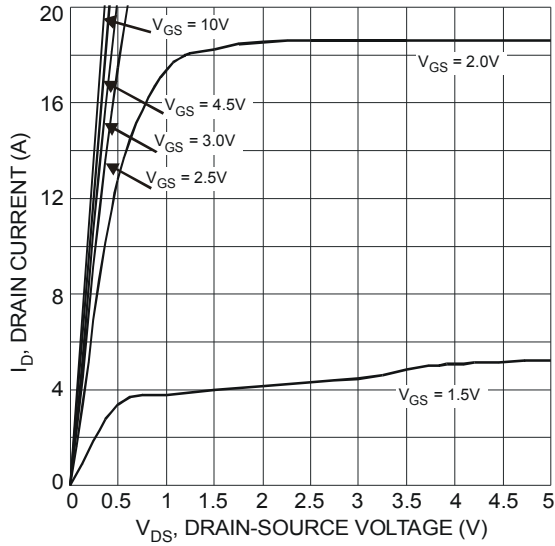


Fig. 1 Typical Output Characteristics

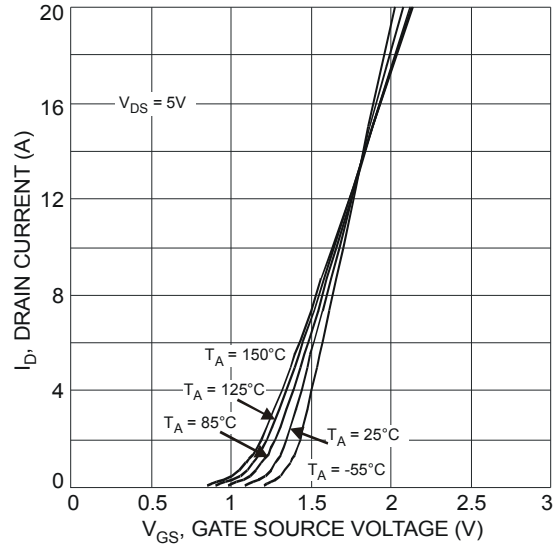


Fig. 2 Typical Transfer Characteristics

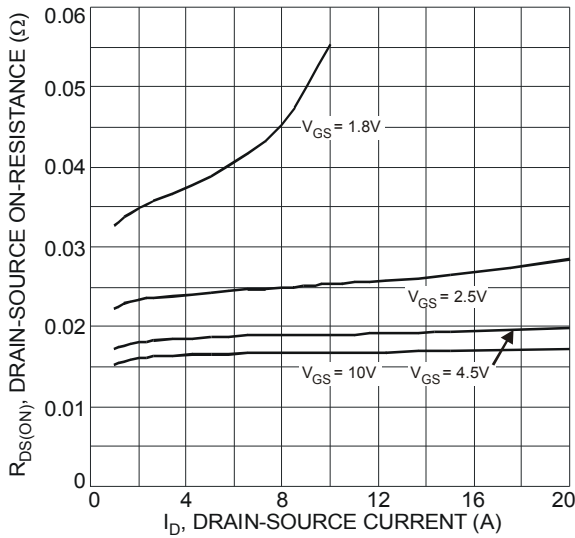


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

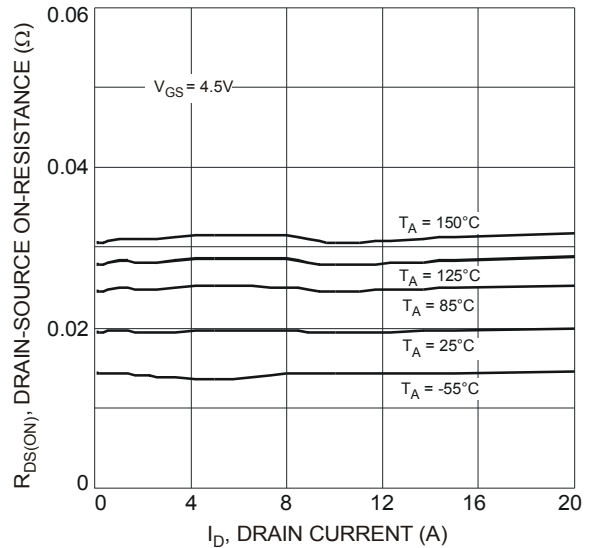


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

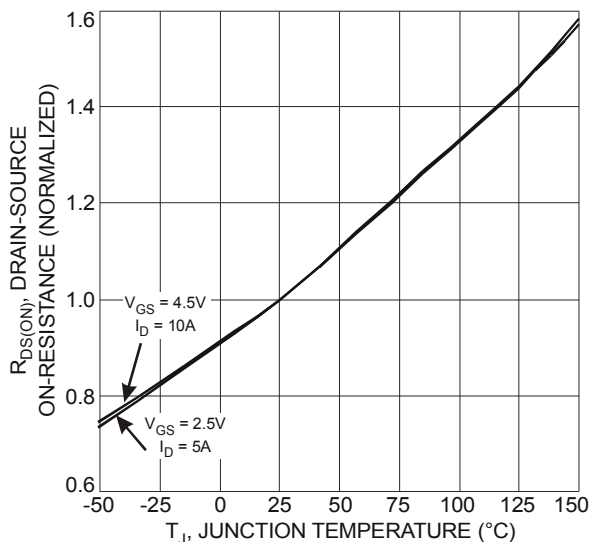


Fig. 5 On-Resistance Variation with Temperature

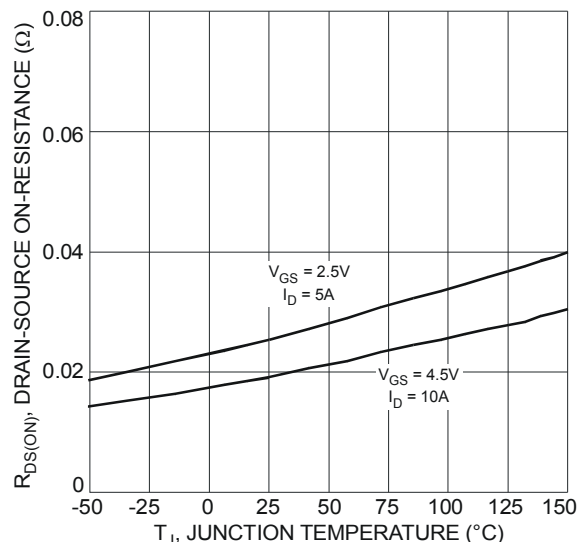


Fig. 6 On-Resistance Variation with Temperature

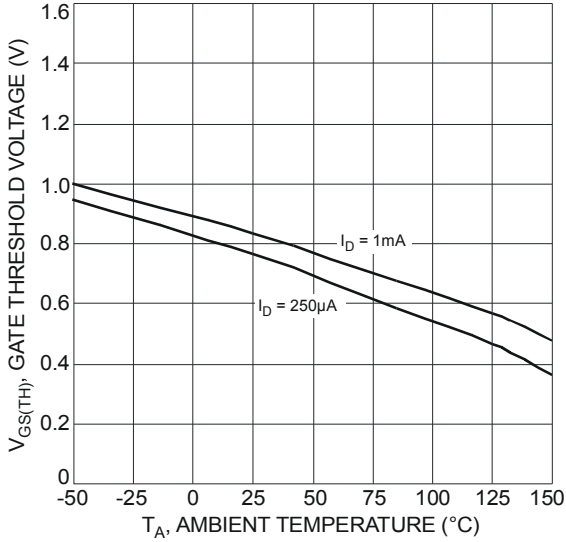


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

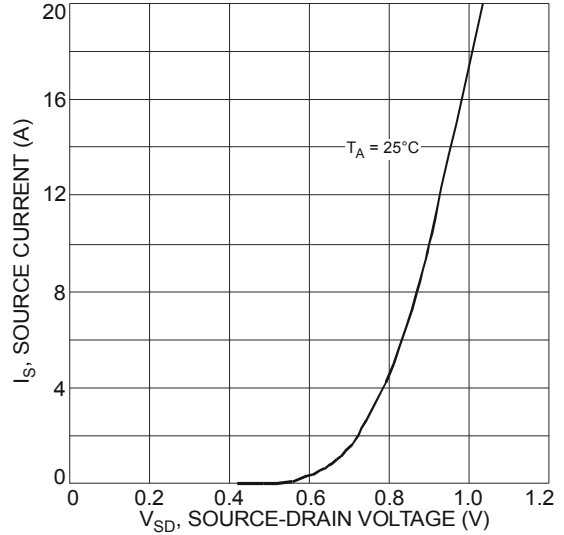


Fig. 8 Diode Forward Voltage vs. Current

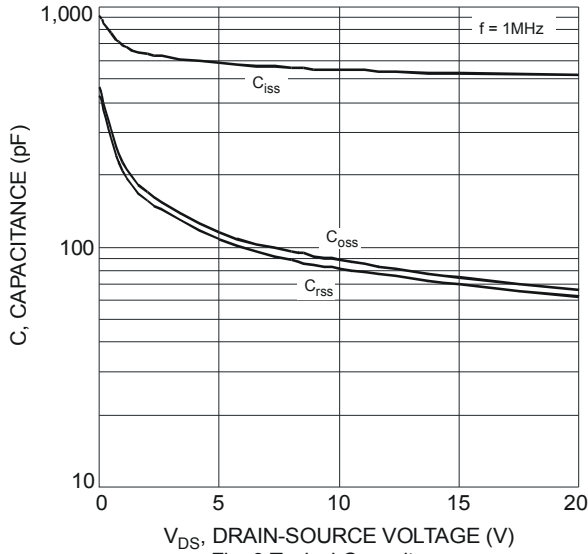


Fig. 9 Typical Capacitance

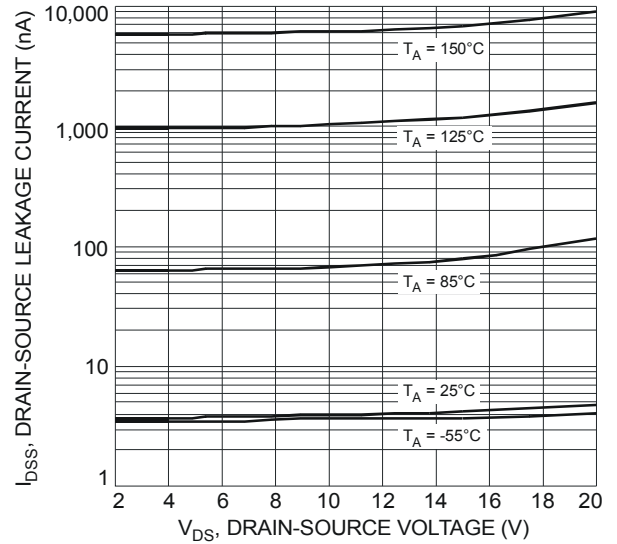


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

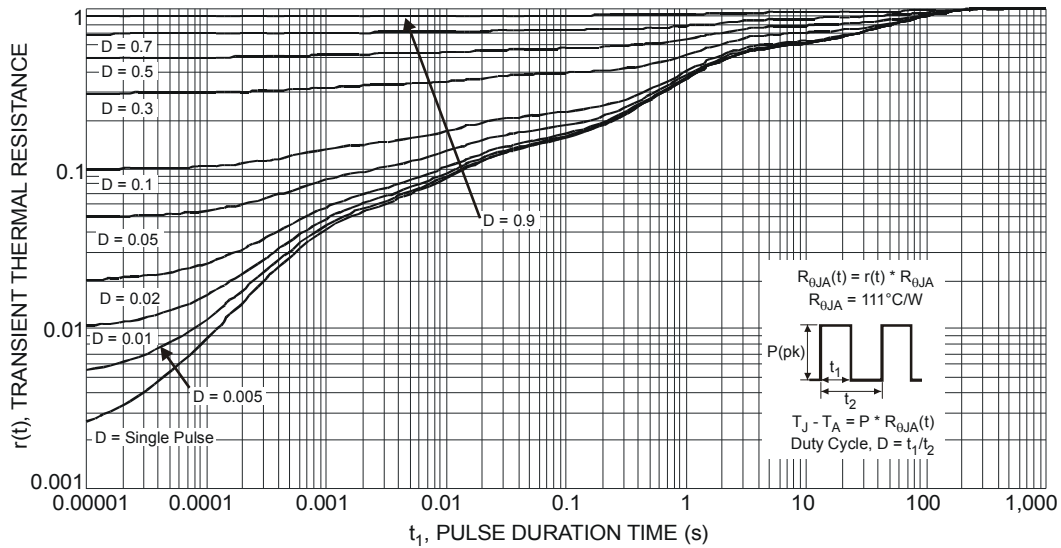
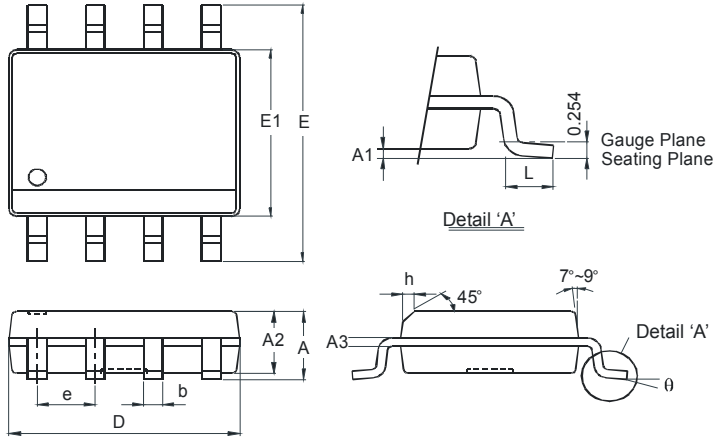


Fig. 11 Transient Thermal Response

**Package Outline Dimensions**

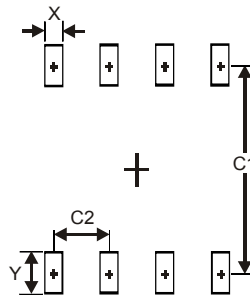
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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